

MOSFET - Power, Single N-Channel

100 V, 12.2 mΩ, 52 A

NVMYS012N10MCL

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	100	V	
Gate-to-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)	Steady State	I_D	$T_C = 25^\circ\text{C}$	52	A
			$T_C = 100^\circ\text{C}$	37	
Power Dissipation $R_{\theta JC}$ (Note 1)	Steady State	P_D	$T_C = 25^\circ\text{C}$	72	W
			$T_C = 100^\circ\text{C}$	36	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	Steady State	I_D	$T_A = 25^\circ\text{C}$	11.6	A
			$T_A = 100^\circ\text{C}$	8.2	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	Steady State	P_D	$T_A = 25^\circ\text{C}$	3.6	W
			$T_A = 100^\circ\text{C}$	1.8	
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM}	283	A	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	60	A	
Single Pulse Drain-to-Source Avalanche Energy ($I_{AS} = 2.6 \text{ A}$)		E_{AS}	218	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

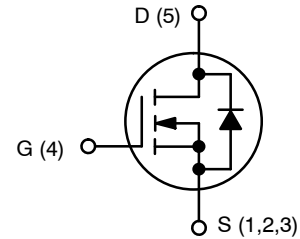
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State	$R_{\theta JC}$	2.1	$^\circ\text{C}/\text{W}$
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	41.2	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$
100 V	12.2 mΩ @ 10 V	52 A
	18.3 mΩ @ 4.5 V	

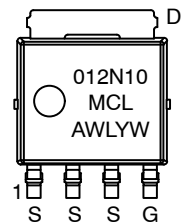


N-CHANNEL MOSFET



LFPAK4
CASE 760AB

MARKING DIAGRAM



012N10MCL = Specific Device Code
 A = Assembly Location
 WL = Wafer Lot
 Y = Year
 W = Work Week

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NVMYS012N10MCL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			60		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 100 V	T _J = 25°C		1.0	μA
			T _J = 125°C		100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V			100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 77 μA	1	1.5	3	V
Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-5.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 14 A	9.7	12.2	mΩ
		V _{GS} = 4.5 V	I _D = 11 A	13.3	18.3	
Forward Transconductance	g _{FS}	V _{DS} = 5 V, I _D = 14 A		51		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 50 V		1338		pF	
Output Capacitance	C _{OSS}			521			
Reverse Transfer Capacitance	C _{RSS}			9.0			
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 50 V; I _D = 14 A		9.0		nC	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 50 V; I _D = 14 A		19		nC	
Threshold Gate Charge	Q _{G(TH)}	V _{GS} = 10 V, V _{DS} = 50 V; I _D = 14 A		2.0		nC	
Gate-to-Source Charge	Q _{GS}			3.0			
Gate-to-Drain Charge	Q _{GD}			3.0			
Plateau Voltage	V _{GP}			2.7			V

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 10 V, V _{DS} = 50 V, I _D = 14 A, R _G = 6.0 Ω		8.4		ns
Rise Time	t _r			2.7		
Turn-Off Delay Time	t _{d(OFF)}			23.8		
Fall Time	t _f			4.6		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 14 A	T _J = 25°C		0.79	1.3	V
			T _J = 125°C		0.66		
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _F = 7 A		40		ns	
Reverse Recovery Charge	Q _{rr}			22		nC	
Charge Time	t _a			19		ns	
Discharge Time	t _b			21		nC	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

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TYPICAL CHARACTERISTICS

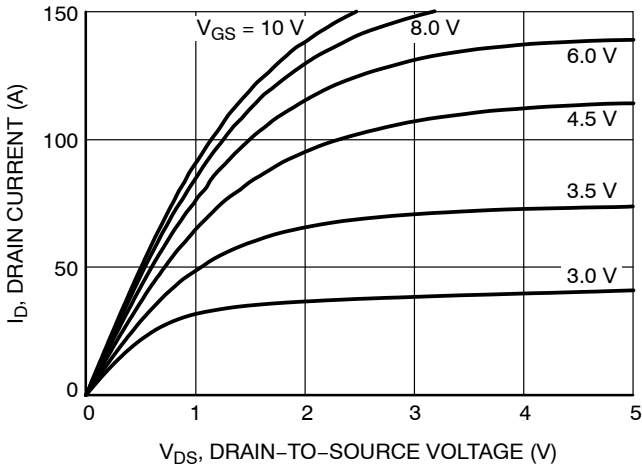


Figure 1. On-Region Characteristics

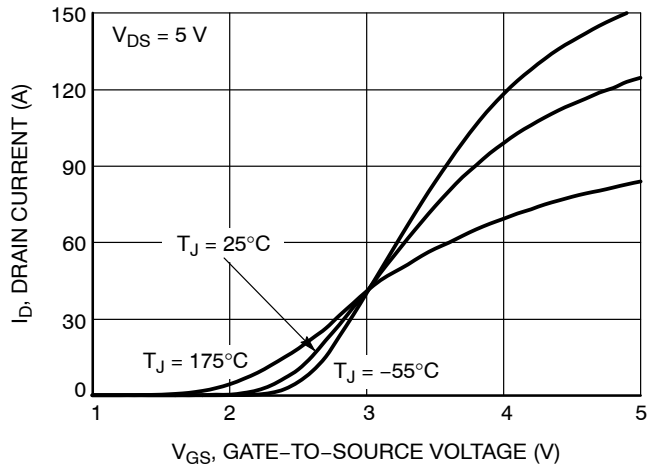


Figure 2. Transfer Characteristics

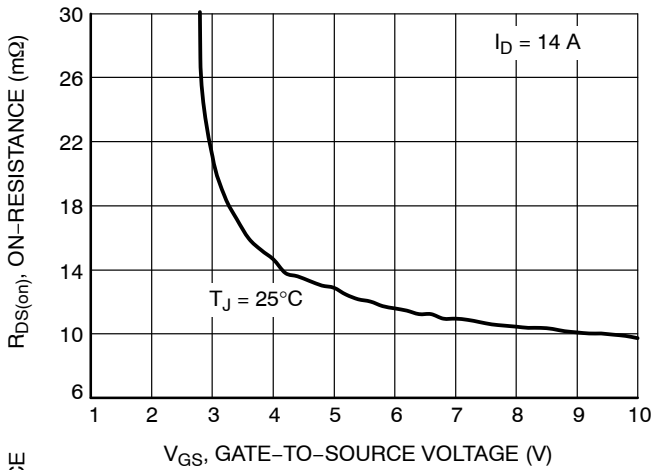


Figure 3. On-Resistance vs. Gate-to-Source Voltage

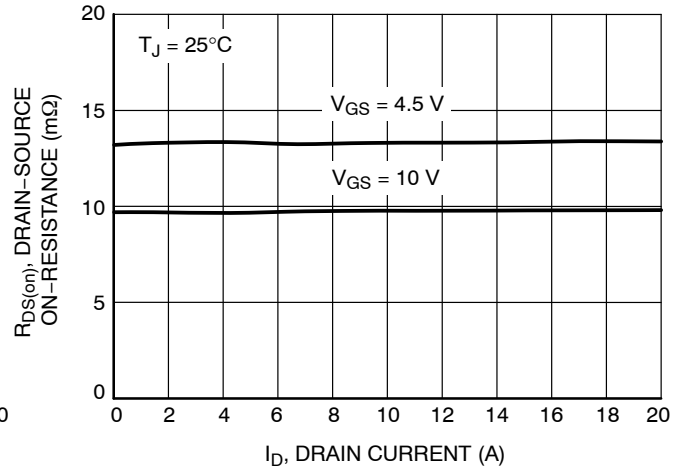


Figure 4. On-Resistance vs. Drain Current

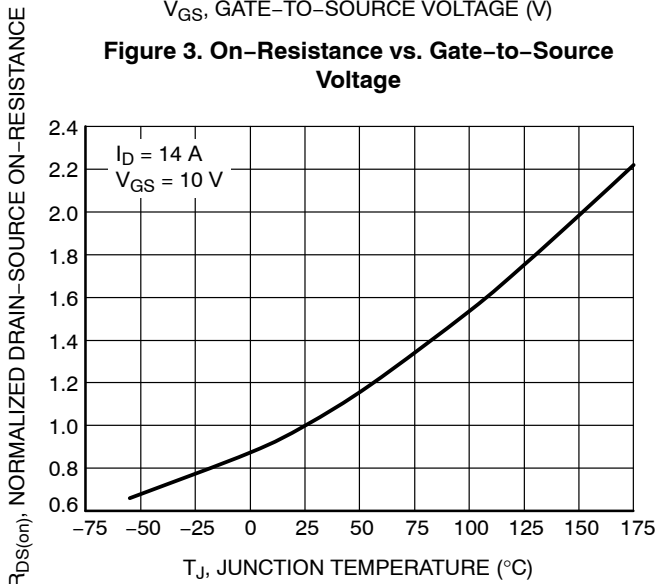


Figure 5. On-Resistance Variation with Temperature

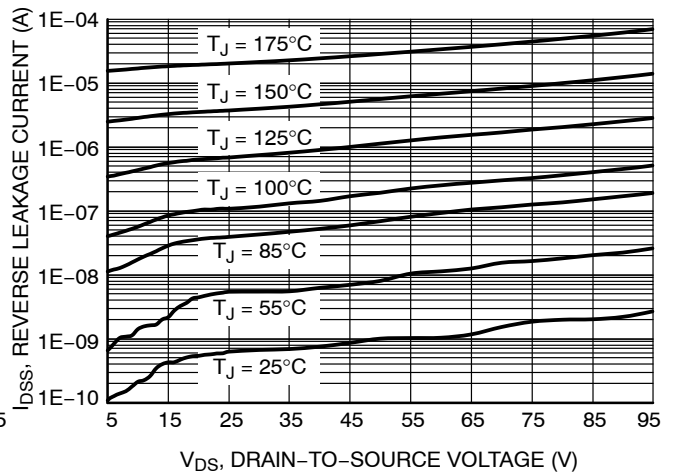


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

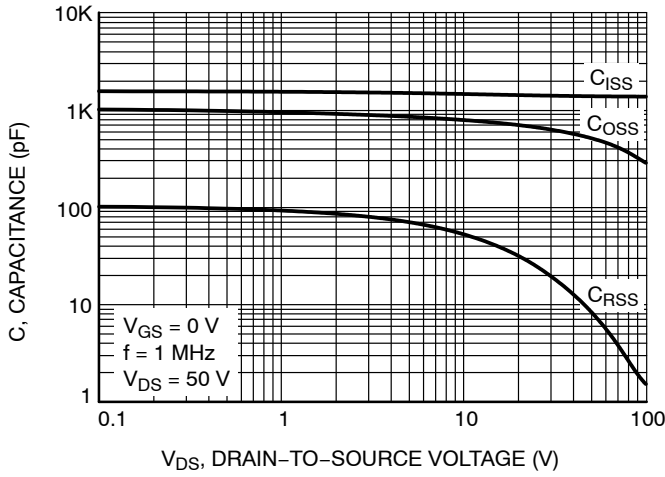


Figure 7. Capacitance Variation

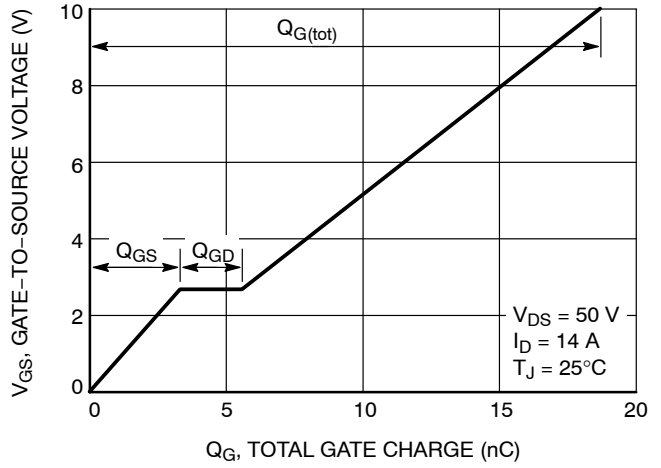


Figure 8. Gate-to-Source Voltage vs. Total Charge

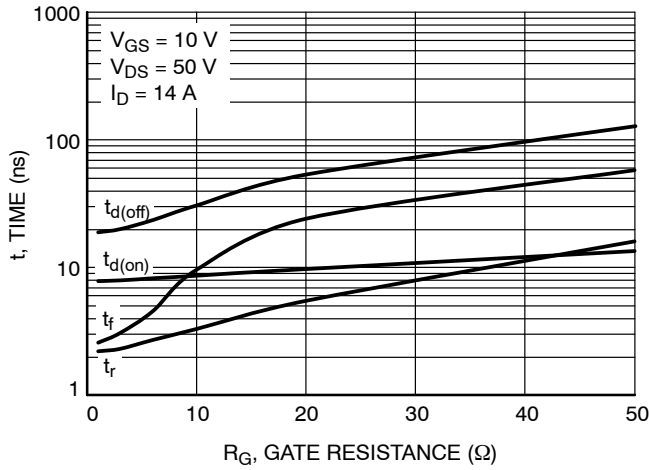


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

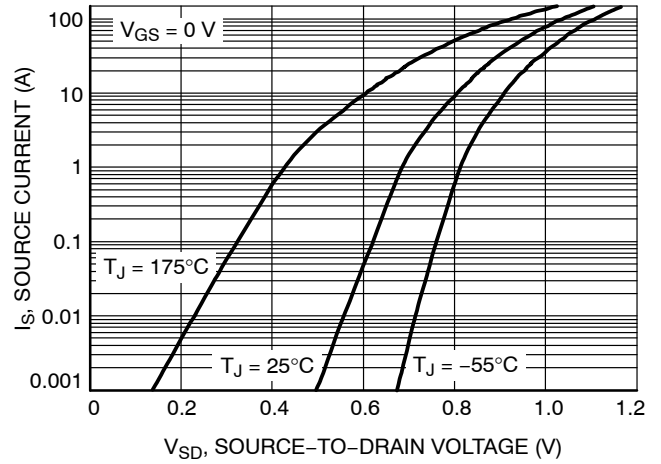


Figure 10. Diode Forward Voltage vs. Current

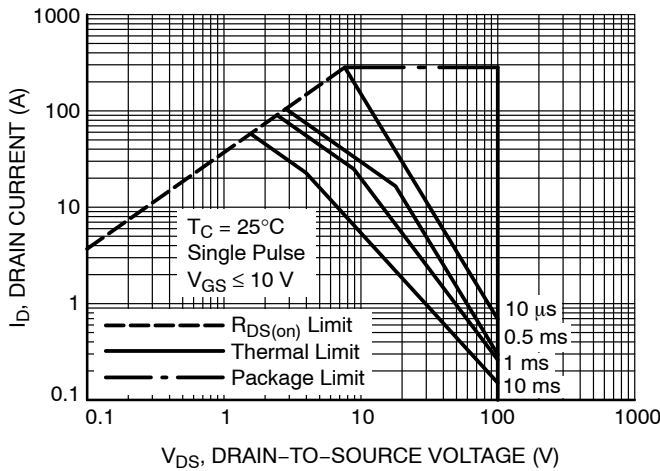


Figure 11. Safe Operating Area

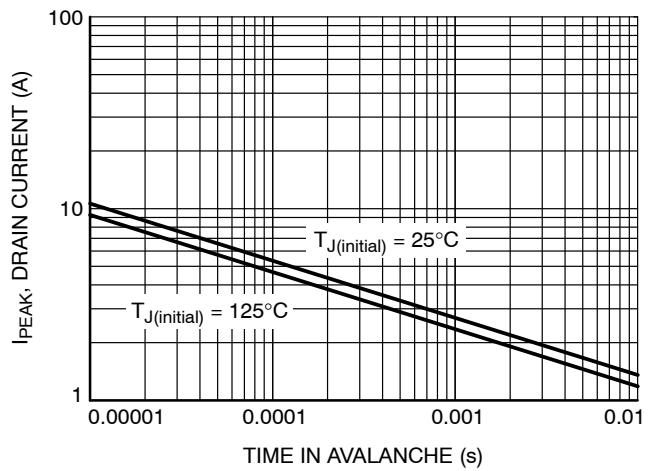


Figure 12. Maximum Drain Current vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

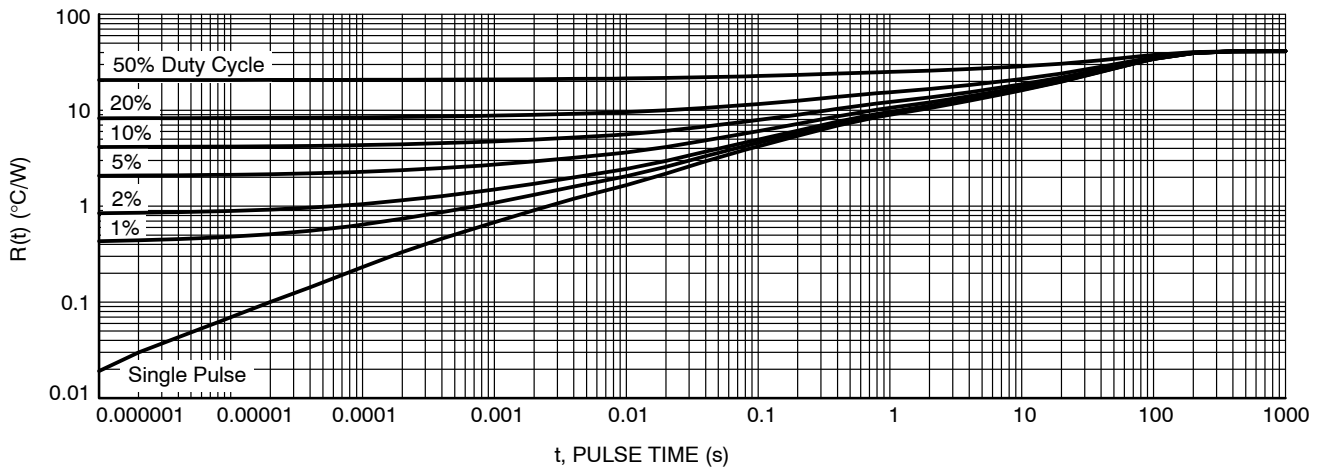


Figure 13. Junction-to-Ambient Transient Thermal Response

DEVICE ORDERING INFORMATION

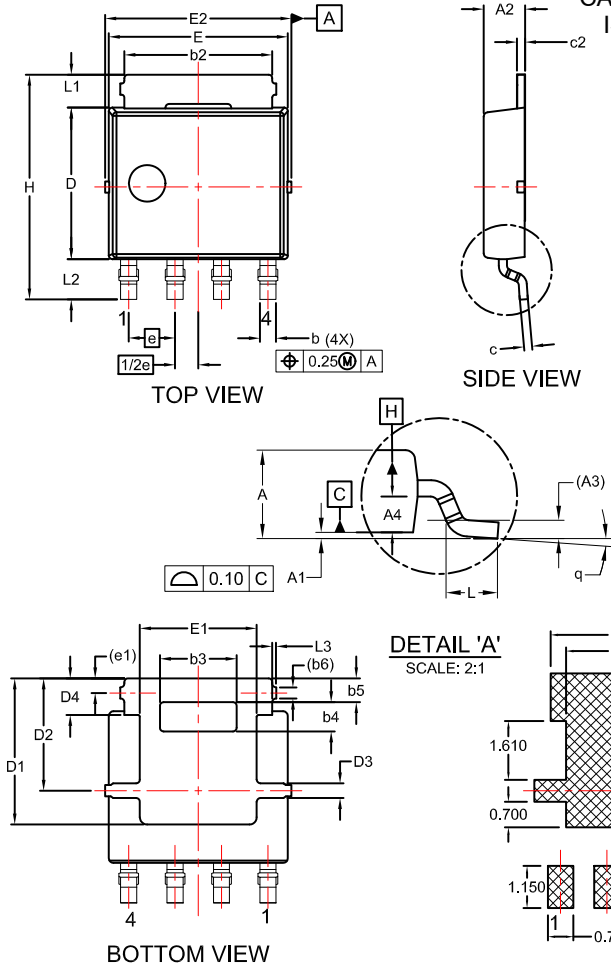
Device	Marking	Package	Shipping [†]
NVMYS012N10MCLTWG	012N10MCL	LFPAK4 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NVMYS012N10MCL

PACKAGE DIMENSIONS

LFP4K4 5x6
CASE 760AB
ISSUE C



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

UNIT IN MILLIMETER			
DIM	MIN	NOM	MAX
A	1.10	1.20	1.30
A1	0.00	0.08	0.15
A2	1.10	1.15	1.20
A3	0.25 REF		
A4	0.45	0.50	0.55
b	0.40	0.45	0.50
b2	3.80	4.10	4.40
b3	2.00	2.10	2.20
b4	0.70	0.80	0.90
b5	0.55	0.65	0.75
b6	0.31 REF		
c	0.19	0.22	0.25
c2	0.19	0.22	0.25
D	4.05	4.15	4.25
D1	3.80	4.00	4.20
D2	3.00	3.10	3.20
D3	0.30	0.40	0.50
D4	0.90	1.00	1.10
E	4.80	4.90	5.00
E1	3.10	3.20	3.30
E2	5.00	5.15	5.30
e	1.27 BSC		
1/2e	0.635 BSC		
e1	0.40 REF		
H	6.00	6.15	6.30
L	0.40	0.65	0.85
L1	0.80	0.90	1.00
L2	0.90	1.10	1.30
L3	0.00	0.10	0.20
q	0°	4°	8°

RECOMMENDED LAND PATTERN

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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